



### **IRFI820G Information**



For Reference Only

Part Number IRFI820G

Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description**MOSFET N-CH 500V 2.1A TO220FP**Package**TO-220-3 Full Pack, Isolated Tab

For the pricing/inventory/lead time, please contact

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Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **IRFI820G Specifications**

Manufacturer Part Number         IRF1820G           Manufacturer         Vishay Siliconix           Category         Discrete Semiconductor Products		
Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  Package  TO-220-3 Full Pack, Isolated Tab  Series  - FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  360pF @ 25V  Vgs (Max)  #20V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  30W (Tc)  Rds On (Max) @ Id, Vgs  3 Ohm @ 1.3A, 10V  Operating Temperature  4-55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3  Package / Case  TO-220-3 Full Pack, Isolated Tab	Manufacturer Part Number	IRFI820G
Package         TO-220-3 Full Pack, Isolated Tab           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         2.1A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         24nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         360pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         30W (Tc)           Rds On (Max) @ Id, Vgs         3 Ohm @ 1.3A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3           Package / Case         TO-220-3 Full Pack, Isolated Tab	Manufacturer	Vishay Siliconix
PackageTO-220-3 Full Pack, Isolated TabSeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C2.1A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs24nC @ 10VInput Capacitance (Ciss) (Max) @ Vds360pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs3 Ohm @ 1.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Category	Discrete Semiconductor Products
Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         2.1A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         24nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         360pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         30W (Tc)           Rds On (Max) @ Id, Vgs         3 Ohm @ 1.3A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3           Package / Case         TO-220-3 Full Pack, Isolated Tab		Transistors - FETs, MOSFETs - Single
FET Type  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  John (Max)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3 Full Pack, Isolated Tab	Package	TO-220-3 Full Pack, Isolated Tab
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C2.1A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs24nC @ 10VInput Capacitance (Ciss) (Max) @ Vds360pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs3 Ohm @ 1.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Series	-
Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C2.1A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs24nC @ 10VInput Capacitance (Ciss) (Max) @ Vds360pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs3 Ohm @ 1.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C2.1A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs24nC @ 10VInput Capacitance (Ciss) (Max) @ Vds360pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs3 Ohm @ 1.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  4V @ 250μA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  30W (Tc)  Rds On (Max) @ Id, Vgs  3 Ohm @ 1.3A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  Package / Case  TO-220-3 Full Pack, Isolated Tab	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  John Capacitance  Through Hole  Supplier Device Package  TO-220-3 Full Pack, Isolated Tab	Current - Continuous Drain (Id) @ 25°C	2.1A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  John Through Hole  Supplier Device Package  TO-220-3  Full Pack, Isolated Tab	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  John Capacitance (Ciss) (Max) @ Vds  30W (Tc)  30W (Tc)  3 Ohm @ 1.3A, 10V  Operating Temperature  John Capacitance (Ciss) (Max) @ Vds  John Capacitance (Ciss) (Max) & John Capacitance (Max) & John Capa	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ±20V  FET Feature -  Power Dissipation (Max) 30W (Tc)  Rds On (Max) @ Id, Vgs 3 Ohm @ 1.3A, 10V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220-3  Package / Case TO-220-3 Full Pack, Isolated Tab	Gate Charge (Qg) (Max) @ Vgs	24nC @ 10V
FET Feature - Power Dissipation (Max) 30W (Tc) Rds On (Max) @ Id, Vgs 3 Ohm @ 1.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Input Capacitance (Ciss) (Max) @ Vds	360pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  3 Ohm @ 1.3A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3  Package / Case  TO-220-3 Full Pack, Isolated Tab	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs3 Ohm @ 1.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3  Package / Case  TO-220-3 Full Pack, Isolated Tab	Power Dissipation (Max)	30W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Rds On (Max) @ Id, Vgs	3 Ohm @ 1.3A, 10V
Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3 Full Pack, Isolated Tab	Mounting Type	Through Hole
	Supplier Device Package	TO-220-3
Report errors?	Package / Case	TO-220-3 Full Pack, Isolated Tab
		Report errors?

#### **IRFI820G Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **IRFI820G Payment Methods**





















# **IRFI820G Shipping Methods**













If you have any question about IRFI820G, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com